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Volume 50, Number 2, February 2011

Rapid Communications

- 020201 **Absorption Change Induced by Electric Field of an InGaAsP/InAlAs/InP Asymmetric Quantum Well Structure Grown on InP Substrates** (2 pages)
Yuichi Kawamura, Takuya Shono
- 020202 **Mechanism of Oxidation on $\text{Si}_2\text{Sb}_2\text{Te}_5$ Phase Change Material and Its Application** (3 pages)
Ting Zhang, Zhitang Song, Yifeng Gu, Yan Cheng, Bo Liu, Songlin Feng
- 020203 **Characterization Method for the Relaxation Process of Metastable Defect States in Cu(In,Ga)Se₂ Thin Films with Photoisothermal Capacitance Transient Spectroscopy** (3 pages)
Hiroshi Okada, Takashi Minemoto
- 020204 **Ultrasonic Spray-Assisted Solution-Based Vapor-Deposition of Aluminum Tris(8-hydroxyquinoline) Thin Films** (3 pages)
Jinchun Piao, Shigetaka Katori, Takumi Ikenoue, Shizuo Fujita
- 020205 **Solution Flow Assisted Fabrication Method of Oriented π -Conjugated Polymer Films by Using Geometrically-Asymmetric Sandwich Structures** (3 pages)
Naoyuki Yamasaki, Yasuo Miyake, Hiroyuki Yoshida, Akihiko Fujii, Masanori Ozaki
- 020206 **Lateral Junction Waveguide-Type Photodiode Grown on Semi-Insulating InP Substrate** (3 pages)
Tadashi Okumura, Daisuke Kondo, Hitomi Ito, SeungHun Lee, Tomohiro Amemiya, Nobuhiko Nishiyama, Shigehisa Arai
- 020207 **Nanosized Structural Anti-Reflection Layer for Thin Film Solar Cells** (3 pages)
Kang-Soo Han, Ju-Hyeon Shin, Kang-In Kim, Heon Lee
- 020208 **Charge-Sensitive Infrared Phototransistors Developed in the Wavelength Range of 10–50 μm** (3 pages)
Takeji Ueda, Yuki Soh, Naomi Nagai, Susumu Komiyama, Hiroshi Kubota
- 020209 **Electric Field Induced Carrier Sweep-Out in Tandem InGaN Multi-Quantum-Well Self-Pulsating Laser Diodes** (3 pages)
Yoshinobu Kawaguchi, Yoshihiko Tani, Pablo O. Vaccaro, Shigetoshi Ito, Hidenori Kawanishi
- 020210 **High Reliability of High-Speed Vertical-Cavity Surface-Emitting Lasers with Silicone-Encapsulated Structure and Parallel Optical Transmitter Modules** (3 pages)
Hiroshi Hatakeyama, Takeshi Akagawa, Kimiyoshi Fukatsu, Kenichiro Yashiki, Keiichi Tokutome, Takayoshi Anan, Masayoshi Tsuji
- 020211 **Simplified Boundary Modeling for Resonating Structures by Scattering Analysis** (3 pages)
Florian Thalmayr, Ken-ya Hashimoto, Masanori Ueda, Tatsuya Omori, Masatsune Yamaguchi
- 020212 **Effects of the pH Level on the Phosphor Characteristics of $\text{Zn}_2\text{SiO}_4:\text{Mn}^{2+}$ Coated with SiO_2 Nanoparticles** (2 pages)
Sujin Han, Jeongheon Seo, Sangho Sohn
- 020213 **Simultaneous Formation of Both Single- and Multi-Wall Carbon Nanotubes by Ultrasonic Spray Pyrolysis** (3 pages)
Ishwor Khatri, Naoki Kishi, Jianhui Zhang, Tetsuo Soga, Takashi Jimbo
- 020214 **New Method of Evaluating the Crystallization Activation Energy of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ by *In situ* Resistance Measurement** (3 pages)
Hyun-Goo Jun, Min-Ho Kwon, Dongmin Kang, Dongbok Lee, Ki-Bum Kim
- 020215 **Thickness-Dependent Structural and Optical Properties of VO₂ Thin Films** (3 pages)
Jianwei Ma, Gang Xu, Lei Miao, Masato Tazawa, Sakae Tanemura
- 020216 **Continuous Monitoring of Electrical Activity of Pancreatic β -Cells Using Semiconductor-Based Biosensing Devices** (3 pages)
Toshiya Sakata, Haruyo Sugimoto

Regular Papers

Semiconductors, dielectrics, and organic materials

- 021001 **Capacitance–Voltage Characteristics of Al₂O₃/AlGaN/GaN Structures and State Density Distribution at Al₂O₃/AlGaN Interface** (7 pages)
Chihoko Mizue, Yujin Hori, Marcin Miczek, Tamotsu Hashizume

(Continued on third cover)

(Continued)

- 021002 Variation of Chemical and Photoluminescence Properties of Mg-Doped GaN Caused by High-Temperature Process (6 pages)
Eri Ogawa, Tamotsu Hashizume
- 021401 Self-Aligned Metal Double-Gate Low-Temperature Polycrystalline Silicon Thin-Film Transistors on Glass Substrate Using Back-Surface Exposure (4 pages)
Akito Hara, Tadashi Sato, Kenji Kondo, Kenta Hirose, Kuninori Kitahara
- 021402 Crystallization Behavior of Sputtered Amorphous Silicon Films by Blue-Multi-Laser-Diode Annealing (5 pages)
Katsuya Shirai, Jean de Dieu Mugiraneza, Toshiharu Suzuki, Tatsuya Okada, Takashi Noguchi, Hideki Matsushima, Takao Hashimoto, Yoshiaki Ogino, Eiji Sahota
- 021501 Correlation Between Tolerance Factor and Temperature Coefficient of Dielectric Constant of $(\text{Ba}, \text{Sr})(\text{Zn}_{1/3}\text{Ta}_{2/3})\text{O}_3$ Dielectric Resonator (6 pages)
Janakiraman Venkatesh, Vemuri Ramakrishna Murthy
- 021502 Effect of Annealing on Optical Absorption of LaAlO_3 at Terahertz Frequencies (3 pages)
Ken-ichi Nomura, Shimpei Okami, Xiaojun Xie, Maya Mizuno, Kaori Fukunaga, Yoshimichi Ohki
- 021503 First-Principles Study on Structural Properties of GeO_2 and SiO_2 under Compression and Expansion Pressure (5 pages)
Shoichiro Saito, Tomoya Ono
- 021601 Large Memory Effect and High Carrier Mobility of Organic Field-Effect Transistors Using Semiconductor Colloidal Nano-Dots Dispersed in Polymer Buffer Layers (5 pages)
Kaori Kajimoto, Atsushi Kurokawa, Kazuyuki Uno, Ichiro Tanaka
- 021602 Influence of Contact Resistance on Effective Mobility in Organic Thin Film Transistor (3 pages)
Ling Li, Paul Heremans, Jin Jang
- 021603 Shape Retention in Polyaniline Artificial Muscles (5 pages)
Keiichi Kaneto, Hikaru Hashimoto, Kazuo Tominaga, Wataru Takashima
- 021701 Effects of Surface Free Energy on Orientational Assembly of Hexaazatrinaphthalene-Based Discotic Mesogen in Sandwich-Type Structure (5 pages)
Wenjun Zheng, Cheng-Yan Chiang, Ya-Ting Hu, Chi Wi Ong
- 021702 Effect of the Polyimide Concentration on the Memory Stability of the Silica-Nanoparticle-Doped Hybrid Aligned Nematic Cell (4 pages)
Chi-Yen Huang, Jian-Hong Chen, Chia-Ting Hsieh, Heng-Cheng Song, Yu-Wu Wang, Lance Horng, Yu-Tai Shih, Shug-June Hwang

Photonics, quantum electronics, optics, and spectroscopy

- 022301 Efficiency Improvement of Organic Solar Cells by Slow Growth and Changing Spin-Coating Parameters for Active Layers (4 pages)
Yu-Sheng Tsai, Wei-Ping Chu, Fuh-Shyung Juang, Rong-Ming Tang, Ming-Hua Chang, Tsung-Eong Hsieh, Mark O. Liu
- 022401 High-Speed Imaging of Broadband Multiplex Coherent Anti-Stokes Raman Scattering Microscopy Using a Supercontinuum Source (4 pages)
Dae Sik Choi, Jang Hyuk Lee, Myoung-Kyu Oh, Tae Jung Eom, Hoon Sup Kim, Hoon Soo Kang, Do-Kyeong Ko
- 022501 Bending Effects of Thermally-Expanded-Core Fiber and Its Application as Variable Optical Attenuator (4 pages)
Hyung Woo Kwon, Jae Won Song, Kwang Taek Kim
- 022502 Efficient Carrier-Envelope Offset Locking with a Simplified Configuration of an *f*-to-*2f* Interferometer (4 pages)
Atsushi Ishizawa, Tadashi Nishikawa, Shinichi Aozasa, Atsushi Mori, Osamu Tadanaga, Masaki Asobe, Hidetoshi Nakano
- 022503 Tandem-Phase Zone-Plate Optics for High-Energy X-ray Focusing (5 pages)
Yasushi Kagoshima, Hidekazu Takano, Takahisa Koyama, Yoshiyuki Tsusaka, Akihiko Saikubo

(Continued on preceding page)

(Continued)

- 022701 **Theoretical Analysis of Length Measurement Using Interference of Multiple Pulse Trains of a Femtosecond Optical Frequency Comb** (5 pages)
Dong Wei, Satoru Takahashi, Kiyoshi Takamasu, Hirokazu Matsumoto
- 022702 **Surface and Interface Modifications of Aluminum Thin Films on Silica Glass Substrate Using 157 nm F₂ Laser for Selective Metallization** (5 pages)
Kazufumi Iwai, Masayuki Okoshi, Hidetoshi Nojiri, Narumi Inoue

Spintronics, superconductivity, and strongly correlated materials

- 023001 **Effect of O⁻ Ion Beam Irradiation during RF-Magnetron Sputtering on Characteristics of CoFeB–MgO Magnetic Tunnel Junctions** (4 pages)
Kazunaga Ono, Norikazu Ohshima, Kazuya Goto, Hiroki Yamamoto, Tadashi Morita, Keizo Kinoshita, Tatsuo Ishii, Hirotaka Toyoda

Device physics

- 024101 **Effect of Series Resistance on Field-Effect Mobility at Varying Channel Lengths and Investigation into the Enhancement of Source/Drain Metallized Thin-Film Transistor Characteristics** (5 pages)
Nguyen Van Duy, Kyunghyun Baek, Dang Ngoc Son, Wonbaek Lee, Kwangryul Kim, Byoungdeog Choi, Hokyun Chung, Junsin Yi
- 024102 **Influence of Surrounding Dielectrics on the Data Retention Time of Doped Sb₂Te Phase Change Material** (3 pages)
Friso Jedema, Michal in 't Zandt, Rob Wolters, Dirk Gravesteijn
- 024103 **A 128 × 96 Pixel Stack-Type Color Image Sensor: Stack of Individual Blue-, Green-, and Red-Sensitive Organic Photoconductive Films Integrated with a ZnO Thin Film Transistor Readout Circuit** (6 pages)
Hokuto Seo, Satoshi Aihara, Toshihisa Watabe, Hiroshi Otake, Toshikatsu Sakai, Misao Kubota, Norifumi Egami, Takahiro Hiramatsu, Tokiyoshi Matsuda, Mamoru Furuta, Takashi Hirao
- 024104 **Effect of Channel Layer Thickness on Characteristics and Stability of Amorphous Hafnium–Indium–Zinc Oxide Thin Film Transistors** (3 pages)
Sun-Jae Kim, Soo-Yeon Lee, Young-Wook Lee, Woo-Geun Lee, Kap-Soo Yoon, Jang-Yeon Kwon, Min-Koo Han
- 024201 **New Driving Scheme to Improve Hysteresis Characteristics of Organic Thin Film Transistor-Driven Active-Matrix Organic Light Emitting Diode Display** (4 pages)
Toshihiro Yamamoto, Yoshiki Nakajima, Tatsuya Takei, Yoshihide Fujisaki, Hirohiko Fukagawa, Mitsunori Suzuki, Genichi Motomura, Hiroto Sato, Shizuo Tokito, Hideo Fujikake
- 024202 **Design Considerations of Nanoscale Schottky Barrier Flash Memory with Source-Side Injection Programming** (7 pages)
Chun-Hsing Shih, Yan-Xiang Luo, Sheng Pin Yeh
- 024301 **Quantum Compact Model of Drain Current in Independent Double-Gate Metal–Oxide–Semiconductor Field-Effect Transistors** (8 pages)
Daniela Munteanu, Jean-Luc Autran, Mathieu Moreau

Nanoscale science and technology

- 025001 **Selective Synthesis of SiC and SiO_x Nanowires by Direct Microwave Irradiation** (4 pages)
Eugene Oh, Seung-Ho Jung, Jaegeun Lee, Seungho Cho, Hye-Jin Kim, Bo-Ram Lee, Kun-Hong Lee, Kyong-Hwa Song, Chi-Hoon Choi, Do-Suck Han
- 025002 **Size Reduction and Phosphorus Doping of Silicon Nanocrystals Prepared by a Very High Frequency Plasma Deposition System** (5 pages)
Yoshifumi Nakamine, Naoki Inaba, Tetsuo Kodera, Ken Uchida, Rui N. Pereira, Andre R. Stegner, Martin S. Brandt, Martin Stutzman, Shunri Oda
- 025003 **Thermoelectric Properties of Double Quantum Dots Embedded in a Nanowire** (5 pages)
David M.-T. Kuo

Crystal growth, surfaces, interfaces, thin films, and bulk materials

- 025501 **Synthesis of a Nitrogen-Doped TiO₂ (Rutile) Single Crystal and Its p-Type Behaviors** (6 pages)
Akiyuki Matsushita, Masahiko Shimoda, Takashi Naka, Yuh Yamada

(Continued on preceding page)

(Continued)

- 025502 **Effect of Evaporation on Protein Crystals Grown in Semi-Solid Agarose Hydrogel** (4 pages)
Shigeru Sugiyama, Mika Hirose, Noriko Shimizu, Mayumi Niijyama, Mihoko Maruyama, Gen Sazaki, Ryota Murai, Hiroaki Adachi, Kazufumi Takano, Satoshi Murakami, Tsuyoshi Inoue, Yusuke Mori, Hiroyoshi Matsumura
- 025601 **Sublattice Rotation of GaP Grown on 2°-Misoriented Si Substrate Using Metalorganic Vapor Phase Epitaxy** (8 pages)
Yasushi Takano, Tatsuru Misaki, Tatsuya Takagi, Hiroki Yamada, Shunro Fuke
- 025602 **Nanoscale Texture Control of Polyelectrolyte Multilayer Using Spray Layer-by-Layer Method** (6 pages)
Kyu-Hong Kyung, Seimeji Shiratori
- 025701 **Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas** (4 pages)
Hitoshi Habuka, Takayuki Nishida
- 025801 **Fabrication of BaTiO₃-Based Dielectrics for Ultrathin-Layer Multilayer Ceramic Capacitor Application by a Modified Coating Approach** (4 pages)
Zhibin Tian, Xiaohui Wang, Yichi Zhang, Tae-Ho Song, Kang Heon Hur, Longtu Li
- 025802 **Piezoelectric Properties of Pb_{0.98}Bi_{0.02}Zr_{0.51}Ti_{0.48}Zn_{0.01}O₃ Ceramics** (4 pages)
Wenze He, Jian Yu
- 025803 **Characteristics of Vanadium Oxide Thin Films Prepared by Metal–Organic Decomposition for Bolometer Detectors** (4 pages)
Le Ngoc Son, Takashi Tachiki, Takashi Uchida

Plasmas, applied atomic and molecular physics, and applied nuclear physics

- 026001 **An EDDY/Particle-in-Cell Simulation of Erosion of Plasma Facing Walls Bombarded by a Collisional Plasma** (7 pages)
Kensuke Inai, Kaoru Ohya
- 026201 **Improvement in Discharge Delay Time by Accumulating Positive Wall Charges on Cathode MgO Protective Layer Surface in Alternating-Current Plasma Display Panels** (10 pages)
Kyohei Yoshino, Takaharu Nagatomi, Yukihiko Morita, Toshiyasu Oue, Naoki Kosugi, Mikihiko Nishitani, Masatoshi Kitagawa, Yoshizo Takai
- 026401 **Electron Cloud Effects in Cornell Electron Storage Ring Test Accelerator and International Linear Collider Damping Ring** (9 pages)
Hyunchang Jin, Moohyun Yoon, Kazuhito Ohmi, John W. Flanagan, Mark A. Palmer
- 026402 **X-ray Angle-Resolved Computed Tomography Using an Asymmetric Analyzer Crystal** (4 pages)
Keiichi Hirano

Device processing, fabrication and measurement technologies, and instrumentation

- 026501 **Fabrication of Electron Passes in Nano-TiO₂ Layer by High-Velocity Oxy-Fuel Method for Dye-Sensitized Solar Cells** (4 pages)
Terumi Nishimura, Daishiro Nomura, Shohhei Sakaguchi, Hideaki Nagayoshi, Shuzi Hayase
- 026502 **Optimum Dissolution Point of Chemically Amplified Resists in Terms of Trade-Off Relationships between Resolution, Line Edge Roughness, and Sensitivity** (5 pages)
Takahiro Kozawa, Hiroki Yamamoto, Seiichi Tagawa
- 026503 **Method to Evaluate the Influence of Etching Damage on Microcantilever Surface on Its Mechanical Properties** (6 pages)
Shinji Ueki, Yuki Nishimori, Hiroshi Imamoto, Tomohiro Kubota, Masakazu Sugiyama, Hideki Kawakatsu, Seiji Samukawa, Gen Hashiguchi
- 026504 **Fabrication of 70-nm-Pitch Two-Level Interconnects by using Extreme Ultraviolet Lithography** (7 pages)
Naofumi Nakamura, Noriaki Oda, Eiichi Soda, Hajime Aoyama, Yuusuke Tanaka, Daisuke Kawamura, Nobuki Hosoi, Yukio Takigawa, Morio Shiohara, Seiichi Kondo, Ichiro Mori, Shuichi Saito
- 026601 **Observation of Biospecimens at Cryotemperatures with Soft X-ray Microscope** (5 pages)
Mitsuhiko Kimura, Kuniko Takemoto, Yoshio Ohashi, Takuji Ohigashi, Koji Nakanishi, Hidetoshi Namba, Hiroshi Kihara

(Continued on preceding page)

(Continued)

Cross-disciplinary areas

- 027001 Charge Accumulation Type Hydrogen Ion Image Sensor with High pH Resolution (5 pages)
Shoko Takenaga, Yui Tamai, Makoto Ishida, Kazuaki Sawada

- 027101 High Power ($\text{Na}_{0.5}\text{K}_{0.5}\text{NbO}_3$ -Based Lead-Free Piezoelectric Transformer (4 pages)
Erkan A. Gurdal, Seyit O. Ural, Hwi-Yeol Park, Sahn Nahm, Kenji Uchino

- 027301 Design of Translation Rotary Ultrasonic Motor with Slanted Piezoelectric Ceramics (8 pages)
Safakcan Tuncdemir, Seyit O. Ural, Burhanettin Koc, Kenji Uchino

Brief Notes

- 028001 Preparation of Highly-Oriented Co_2MnSi Films on a Non-Single-Crystalline Substrate Using a Titanium-Nitride Buffer Layer (2 pages)
Atsushi Sugihara, Yuya Sakuraba, Kay Yakushiji, Shinji Yuasa, Koki Takanashi

- 028002 Structural Property of Pentacene Film Prepared by Hydrogen Chemical Transport Deposition (2 pages)
Akira Heya, Hiroshi Hasegawa, Naoto Matsuo

Dependence of the structural properties of pentacene film on the deposition temperature was studied. The optical absorption coefficient of pentacene film prepared at 400 °C was found to be low because the pentacene molecules were easily sublimated from a source but did not deposit. Therefore, a high annealing temperature is required for the enhanced application of pentacene film as an active layer in organic electronic devices. In addition, the pentacene film is suitable for a low-temperature deposition. Moreover, the optical absorption coefficient of the pentacene film was found to increase with the annealing temperature up to 400 °C. However, the optical absorption coefficient of pentacene film prepared at 400 °C was found to decrease to the value of 400 °C due to the sublimation of pentacene molecules.

We have developed a novel deposition method for the fabrication of pentacene film using a hydrogen chemical transport deposition (HTCD) method. In this method, a pentacene source was heated and a source of pentacene molecules were transferred to the growth chamber through heat transfer. This is a simple and efficient synthesis method for the formation of pentacene film.

In this article, we report the deposition of pentacene film on ITO substrates over a wide range of annealing temperatures. The optical absorption coefficient of pentacene film prepared at 400 °C was found to be high, which is due to the pentacene film being well oriented and called "single crystal" because it has a single crystal orientation.

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Fig. 1. Optical microscopy



Fig. 2. Optical microscopy

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